

isc Silicon PNP Power Transistor

2SB861

DESCRIPTION

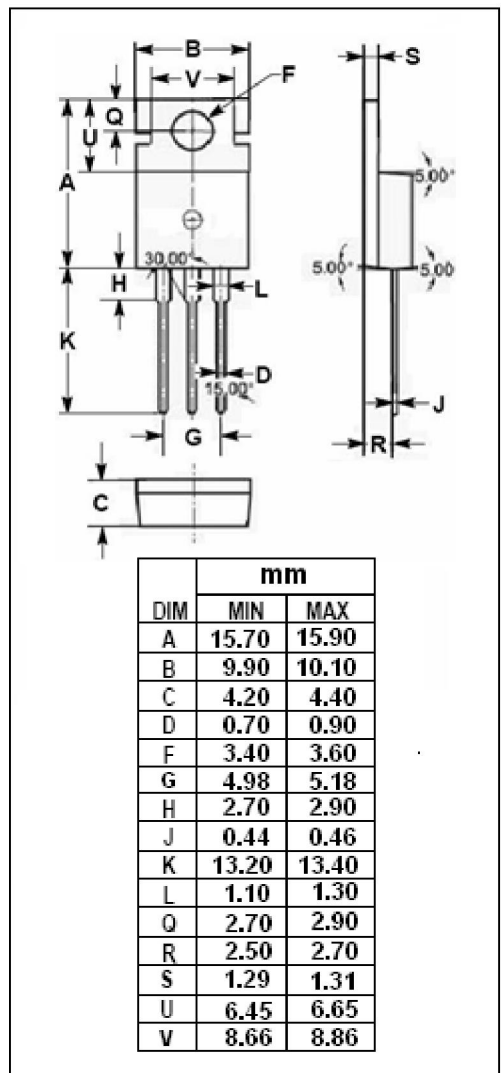
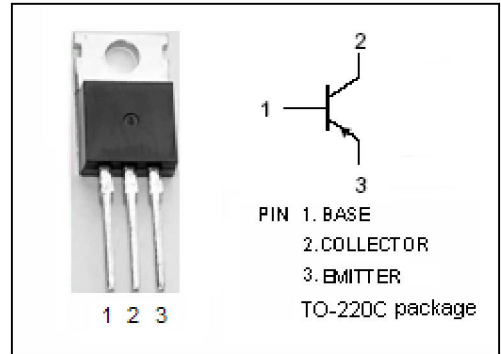
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SD1138

APPLICATIONS

- Developed for low frequency power amplifier color TV vertical deflection output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.8	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB861****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}$; $R_{BE} = \infty$	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -5\text{mA}$; $I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$; $I_B = -50\text{mA}$			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -50\text{mA}$; $V_{CE} = -4\text{V}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}$; $I_E = 0$			-1	μA
h_{FE-1}	DC Current Gain	$I_C = -50\text{mA}$; $V_{CE} = -4\text{V}$	60		200	
h_{FE-2}	DC Current Gain	$I_C = -500\text{mA}$; $V_{CE} = -10\text{V}$	60			
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -100\text{V}$; $f_{test} = 1.0\text{MHz}$		30		pF

◆ h_{FE-1} Classifications

B	C
60-120	100-200

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